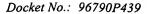
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Application No. 10/665,515 TRANSMITTAL FORM Filing Date September 16, 2003 (to be used for all correspondence after initial filing) First Named Inventor Takashi Matsuoka Art Unit **Examiner Name** Total Number of Pages in This Submission 20 Attorney Docket Number 96790P439 **ENCLOSURES** (check all that apply) After Allowance Communication Fee Transmittal Form Drawing(s) to Group Appeal Communication to Board of Appeals and Interferences Fee Attached Licensing-related Papers Appeal Communication to Group Petition Amendment / Response (Appeal Notice, Brief, Reply Brief) Petition to Convert a Provisional Application After Final Proprietary Information Affidavits/declaration(s) Power of Attorney, Revocation Change of Correspondence Address Status Letter Extension of Time Request Other Enclosure(s) **Terminal Disclaimer** (please identify below): **Express Abandonment Request** Request for Refund Prior Art References (12); Information Disclosure Statement return postcard PTO/SB/08 CD, Number of CD(s) Certified Copy of Priority Document(s) Response to Missing Parts/ Incomplete Application Remarks Basic Filing Fee Declaration/POA Response to Missing Parts under 37 CFR 1.52 or 1.53 SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT Firm Eric S. Hyman, Reg. No. 30,139 Individual name BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP Signature Date **CERTIFICATE OF MAILING/TRANSMISSION** I hereby certify that this correspondence is being deposited with the United States Postal Service on the date shown below with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450. Typed or printed name Melissa Stead 10/0-03 Signature Date





the Application of:

TAKASHI MATSUOKA, ET AL.

Application No.: 10/665,515

Filed: September 16, 2003

For: SEMICONDUCTOR OPTICAL MODULATOR AND LASER

WITH OPTICAL MODULATOR

Art Group:

Examiner:

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

In accordance with the duty of disclosure, enclosed is a copy of Information Disclosure Statement by Applicant (form PTO/SB/08), which is being submitted within three (3) months of filing of the application. It is respectfully requested that the cited references be considered and that the enclosed copy of PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

-1- 96790P439

The submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made in the subject application and is not to be construed as an admission that the information cited in this statement is material to patentability.

Please charge any fees due to Deposit Account 02-2666. A duplicate copy of the Fee Transmittal (PTO/SB/17) is enclosed for this purpose.

		Respectfully submitted,
		BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP
Date:	c=10107	
		Eric S. Hyman, Reg. No. 30,139

12400 Wilshire Blvd., 7th Floor Los Angeles, California 90025 (310) 207-3800

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Melissa Stead Date

-2- 96790P439



Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

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Сотр	lete if Known	
Application Number		
Filing Date		
First Named Inventor	Takashi Matsuoka	
Art Unit		
Examiner Name		
Attorney Docket Number		

U.S.PATENT DOCUMENT						
Examiner Cite	Document I	Number	Publication Date	Name of Patentee or Applicant		
Initials*	No.¹	Number	Kind Code ²	MM-DD-YYYY	of Cited Document	
		US 5,923,688	JP	07-13-1999	NEC Corporation	
		US				
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FOREIGN PATENT DOCUMENT							
Examiner	Cite	Foreign Patent Document Public		Publication Date	Name of Patentee	- 6	
Initials*	No.¹	Country Code ³	Number⁴	KindCode ⁵	MM-DD-YYYY	or Applicant of Cited Document	Tranlation ⁶
		JP	08-086978	Α	04-02-1996	NTT CORPORATION	ABST
		JP	10-294532	Α	11-04-1998	TOSHIBA CORP	ABST
		JP	2002-176196	Α	06-21-2002	NGK INSULATORS LTD	ABST
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¹Applicant's unique citation designation number (optional). ²See Kinds Codes of USPTO Patent Documents at www.uspto.gov, MPEP901.04 or in the comment box of this document. ³Enter office that issued the document, by the two-letter code (WIPO Standard ST.3) ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁵Applicant is to indicate here if English language Translation is attached.

		no.			P TO/SB/06B (Modified)
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ST	TATEMENT E	BY APPLICA	ANT	First Named Inventor	Takashi Matsuoka
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				Examiner Name	
Sheet	1	of	1	Attorney Docket Number	

		OTHER PRIOR ART-NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No.¹	Include name of the author (in CAPITAL LETTERS), title of the article (whenappropiate), title of the item (book, magazine, journal, serial, symposium catalog, etc.), date, page(s, volume-issue number(s), publisher, city and/or country where published.	Translation ²
		Bernardini et al., "Spontaneous polarization and piezoelectric constants of III-V nitrides", Phys. Rev. B, 56 (1997) R10024	
		Osamura et al., "Fundamental absorption edge GaN, InN and their alloys", Solid State Comm., 11(1972)617	
		Puychevrier et al., "Synthesis of III-V semiconductor nitrides by reactive cathodic sputtering", Thin Solid Films, 36(1976)141	
		Tansley et al., "Optical band gap of indium nitride", J Appl. Phys., 59(1986)3241	
		Matsuoka et al., "Wide-Gap Semiconductor (In, Ga) N", International Symposium	
		on GaAs and Related Compounds, (Karuizawa, Japan, 1989); in Inst. Phys. Conf. Ser., 106. pp. 141 - 146	
		Matsuoka, "Phase Separation in Wurtzite In _{1-x-y} Ga _x Al _y N",MRS Internet J. Nitride Semicond. Res. 3,54(1998)	
		Matsuoka et al., "OPTICAL BANDGAP ENERGY OF InN", Extended Abstracts(the 36 th Meeting,); The Japan Society of Applied Physics and Related Societies, pp. 270 (1p-ZN-9) (1998)	
		Matsuoka et al., "OPTICAL BANDGAP ENERGY OF InN", Extended Abstracts(the 49 th Spring Meeting, 2002); The Japan Society of Applied Physics and Related Societies, pp. 392 (29p-ZM-1)	
	-		

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